**Product data sheet** 

# 1. General description

Planar passivated four quadrant triac in a SOT78 (TO-220AB) plastic package intended for use in applications requiring high bidirectional transient and blocking voltage capability and high thermal cycling performance.

## 2. Features and benefits

- · High blocking voltage capability
- High noise immunity
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants

# 3. Applications

- General purpose motor control
- · General purpose switching

# 4. Quick reference data

#### Table 1. Quick reference data

| Symbol              | Parameter                                | Conditions   | ons Values |     |     |      |
|---------------------|--|--|------------|-----|-----|------|
| Absolute            | maximum rating                           |  |            |     |     |      |
| $V_{DRM}$           | repetitive peak off-state voltage        |  |            | 600 |     | V    |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; T <sub>mb</sub> ≤ 91 °C;<br>Fig. 1; Fig. 2; Fig. 3                             | 25         |     |     | А    |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25 ^{\circ}\text{C}$ ;<br>$t_p = 20 \text{ms}$ ; Fig. 4; Fig. 5 | 190        |     | А   |      |
| Symbol              | Parameter                                | Conditions   | Min        | Тур | Max | Unit |
| Static ch           | aracteristics                            |  |            |     |     |      |
| I <sub>GT</sub>     | gate trigger current                     | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G+;$<br>$T_j = 25 \text{ °C; } Fig. 7$        | -          | 6   | 35  | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2+ G-;}$<br>$T_j = 25 \text{ °C; Fig. 7}$           | -          | 10  | 35  | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$<br>$T_j = 25 \text{ °C; } Fig. 7$          | -          | 11  | 35  | mA   |
|                     |  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G+;}$<br>$T_j = 25 \text{ °C; } Fig. 7$          | -          | 23  | 70  | mA   |

4Q Triad

# 5. Pinning information

**Table 2. Pinning information** 

| Graphic symbol |
|----------------|
|                |
| T2T1           |
| sym051         |
| symus i        |
|                |
|                |
|                |

# 6. Ordering information

### **Table 3. Ordering information**

| Type number |            | Package  |   |         |  |  |  |  |
|-------------|------------|----------|---|---------|--|--|--|--|
|             |            | Name     | Description   | Version |  |  |  |  |
|             | BTA140-600 | TO-220AB | plastic single-ended package; heatsink mounted;<br>1 mounting hole; 3-lead TO-220AB | SOT78   |  |  |  |  |

# 7. Marking

## **Table 4. Marking codes**

| Type number | Marking codes |
|-------------|---------------|
| BT140-600   | BT140-600     |

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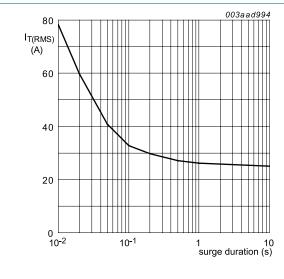
# 8. Limiting values

### Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol              | Parameter                                | Conditions   | Values     | Unit             |
|---------------------|--|--|------------|------------------|
| $V_{DRM}$           | repetitive peak off-state voltage        |  | 600        | V                |
| I <sub>T(RMS)</sub> | RMS on-state current                     | full sine wave; T <sub>mb</sub> ≤ 91°C;<br>Fig 1; Fig 2; Fig 3                                 | 25         | А                |
| I <sub>TSM</sub>    | non-repetitive peak on-<br>state current | full sine wave; $T_{j(init)} = 25  ^{\circ}\text{C}$ ;<br>$t_p = 20  \text{ms}$ ; Fig 4; Fig 5 | 190        | А                |
|                     |  | full sine wave; $T_{j(init)} = 25  ^{\circ}\text{C}$ ; $t_p = 16.7  \text{ms}$                 | 209        | А                |
| l²t                 | I <sup>2</sup> t for fusing              | t <sub>p</sub> = 10 ms; SIN  | 180        | A <sup>2</sup> s |
| dl <sub>⊤</sub> /dt | rate of rise of on-state current         | I <sub>G</sub> = 70 mA; T2+ G+   | 50         | A/µs             |
|                     |  | I <sub>G</sub> = 70 mA; T2+ G-   | 50         | A/µs             |
|                     |  | I <sub>G</sub> = 70 mA; T2- G-   | 50         | A/µs             |
|                     |  | I <sub>G</sub> = 140 mA; T2- G+  | 10         | A/µs             |
| I <sub>GM</sub>     | peak gate current                        |  | 2          | Α                |
| $P_{\text{GM}}$     | peak gate power                          |  | 5          | W                |
| $P_{G(AV)}$         | average gate power                       | over any 20 ms period  | 0.5        | W                |
| T <sub>stg</sub>    | storage temperature                      |  | -40 to 150 | °C               |
| T <sub>j</sub>      | junction temperature                     |  | 125        | °C               |

**4Q Triac** 

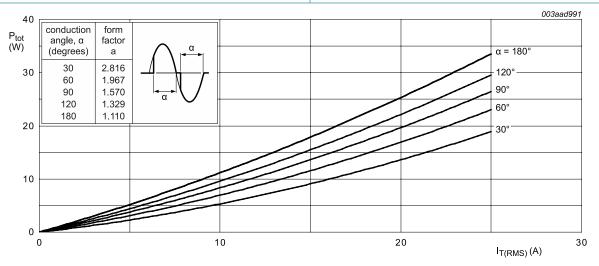


f = 50 Hz;  $T_{mb}$  = 91 °C

30 003aad995
I<sub>T(RMS)</sub>
(A)
20
10
0-50 0 50 100 T<sub>mb</sub>(°C)

Fig. 2. RMS on-state current as a function of mounting base temperature; maximum values

Fig. 1. RMS on-state current as a function of surge duration; maximum values



 $\alpha$  = conduction angle

 $a = form factor = I_{T(RMS)} / I_{T(AV)}$ 

Fig. 3. Total power dissipation as a function of RMS on-state current; maximum values

**4Q Triac** 

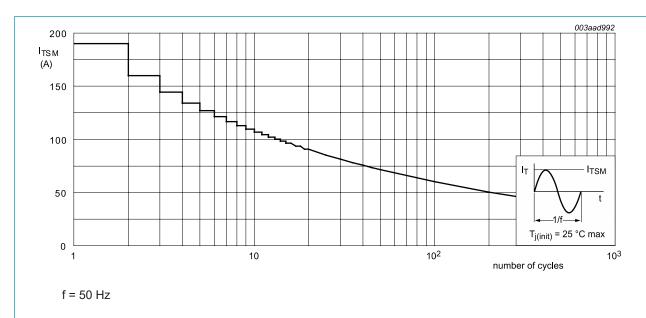
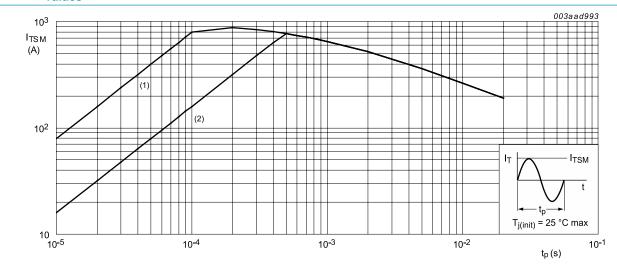


Fig. 4. Non-repetitive peak on-state current as a function of the number of sinusoidal current cycles; maximum values



t<sub>p</sub> ≤ 20 ms

- (1) dl<sub>⊤</sub>/dt limit
- (2) T2- G+ quadrant limit

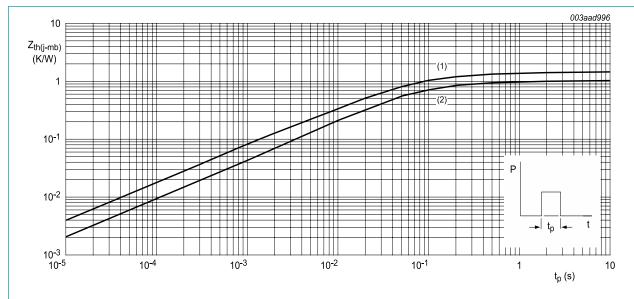
Fig. 5. Non-repetitive peak on-state current as a function of pulse width; maximum values

**4Q Triac** 

# 9. Thermal characteristics

**Table 6. Thermal characteristics** 

| Symbol                | Parameter   | Conditions               | Min | Тур | Max | Unit |
|-----------------------|---|--------------------------|-----|-----|-----|------|
| $R_{\text{th(j-mb)}}$ | thermal resistance                                | full cycle; Fig 6        | -   | -   | 1   | K/W  |
|                       | from junction to mounting base                    | half cycle; <u>Fig 6</u> | -   | -   | 1.4 | K/W  |
| R <sub>th(j-a)</sub>  | thermal resistance<br>from junction to<br>ambient | in free air              | -   | 60  | -   | K/W  |



- (1) Unidirectional (half cycle)
- (2) Bidirectional (full cycle)

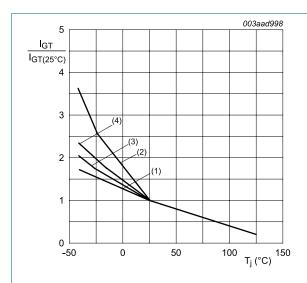
Fig. 6. Transient thermal impedance from junction to mounting base as a function of pulse width

**4Q Triac** 

# 10. Characteristics

## **Table 7. Characteristics**

| Symbol                 | Parameter                             | Conditions   | Min  | Тур | Max  | Unit |
|------------------------|---------------------------------------|--|------|-----|------|------|
| Static ch              | aracteristics                         |  |      |     |      |      |
| I <sub>GT</sub>        | gate trigger current                  | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2+ G+;$<br>$T_j = 25 \text{ °C; } Fig. 7$                                 | -    | 6   | 35   | mA   |
|                        |                                       | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; } T2 + G-;$<br>$T_j = 25 \text{ °C; } Fig. 7$                                | -    | 10  | 35   | mA   |
|                        |                                       | $V_D = 12 \text{ V; } I_T = 0.1 \text{ A; T2- G-;}$<br>$T_j = 25 \text{ °C; } Fig. 7$                                  | -    | 11  | 35   | mA   |
|                        |                                       | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T2- G+;$<br>$T_j = 25 \text{ °C}; Fig. 7$                                    | -    | 23  | 70   | mA   |
| I <sub>L</sub>         | latching current                      | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G+;$<br>$T_j = 25 \text{ °C}; Fig. 8$                                    | -    | 8   | 40   | mA   |
|                        |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2+ G-;$<br>$T_j = 25 \text{ °C}; Fig. 8$                                    | -    | 30  | 60   | mA   |
|                        |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G-;$<br>$T_j = 25 \text{ °C}; Fig. 8$                                    | -    | 18  | 40   | mA   |
|                        |                                       | $V_D = 12 \text{ V}; I_G = 0.1 \text{ A}; T2- G+;$<br>$T_j = 25 \text{ °C}; Fig. 8$                                    | -    | 15  | 60   | mA   |
| I <sub>H</sub>         | holding current                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2+; <u>Fig. 9</u>  | -    | 7   | 60   | mA   |
|                        |                                       | V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; T2-; <u>Fig. 9</u>  |      | 12  | 60   | mA   |
| V <sub>T</sub>         | on-state voltage                      | I <sub>T</sub> = 30 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>  | -    | 1.3 | 1.55 | V    |
| $V_{GT}$               | gate trigger voltage                  | $V_D = 12 \text{ V}; I_T = 0.1 \text{ A}; T_j = 25 \text{ °C};$<br>Fig. 11   | -    | 0.7 | 1    | V    |
|                        |                                       | $V_D = 400 \text{ V}; I_T = 0.1 \text{ A}; T_j = 125 \text{ °C};$<br>Fig. 11   | 0.25 | 0.4 | -    | V    |
| I <sub>D</sub>         | off-state current                     | V <sub>D</sub> = 600 V; T <sub>j</sub> = 125 °C  | -    | 0.1 | 0.5  | mA   |
| Dynamic                | characteristics                       |  |      | •   |      |      |
| dV <sub>D</sub> /dt    | rate of rise of off-state voltage     | $V_{DM}$ = 402 V; $T_{j}$ = 125 °C; $(V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit            | 100  | 300 | -    | V/µs |
| dV <sub>com</sub> /dt  | rate of change of commutating voltage | $V_D = 400 \text{ V}; T_j = 95 \text{ °C}; dI_{com}/dt = 9 \text{ A/}$<br>ms; $I_T = 25 \text{ A}; gate open circuit}$ | -    | 10  | -    | V/µs |
| <b>t</b> <sub>gt</sub> | gate-controlled turn-on time          | $I_{TM} = 30 \text{ A}; V_D = 600 \text{ V}; I_G = 0.1 \text{ A}; dI_G/dt = 5 \text{ A/}\mu\text{s}$                   | -    | 2   | -    | μs   |



- (1) T2+ G+
- (2) T2+ G-
- (3) T2- G-
- (4) T2- G+

Fig. 7. Normalized gate trigger current as a function of junction temperature

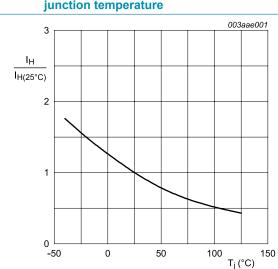


Fig. 9. Normalized holding current as a function of junction temperature

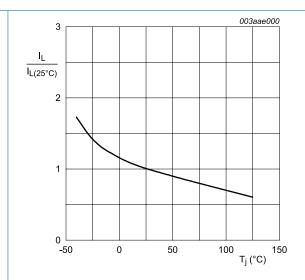
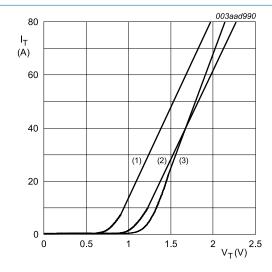


Fig. 8. Normalized latching current as a function of junction temperature



 $V_o$  = 1.073 V;  $R_s$  = 0.015  $\Omega$ 

(1)  $T_j = 125$  °C; typical values (2)  $T_j = 125$  °C; maximum values (3)  $T_j = 25$  °C; maximum values

Fig. 10. On-state current as a function of on-state voltage

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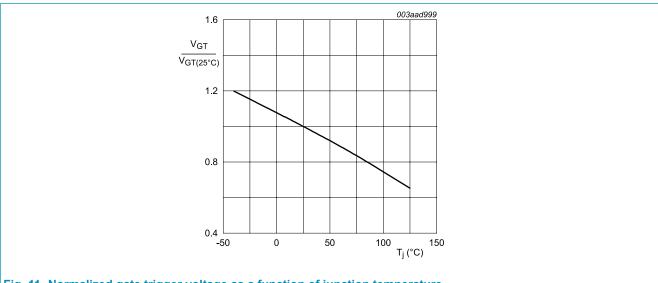
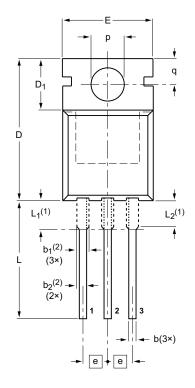


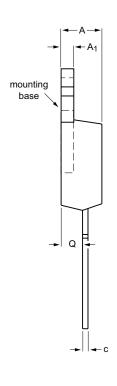
Fig. 11. Normalized gate trigger voltage as a function of junction temperature

# 11. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

**SOT78** 





### **DIMENSIONS** (mm are the original dimensions)

| UNIT | Α          | A <sub>1</sub> | b          | b <sub>1</sub> <sup>(2)</sup> | b <sub>2</sub> <sup>(2)</sup> | С          | D            | D <sub>1</sub> | E           | е    | L            | L <sub>1</sub> <sup>(1)</sup> | L <sub>2</sub> <sup>(1)</sup> max. | р          | q          | Q          |
|------|------------|----------------|------------|-------------------------------|-------------------------------|------------|--------------|----------------|-------------|------|--------------|-------------------------------|------------------------------------|------------|------------|------------|
| mm   | 4.7<br>4.1 | 1.40<br>1.25   | 0.9<br>0.6 | 1.6<br>1.0                    | 1.3<br>1.0                    | 0.7<br>0.4 | 16.0<br>15.2 | 6.6<br>5.9     | 10.3<br>9.7 | 2.54 | 15.0<br>12.8 | 3.30<br>2.79                  | 3.0                                | 3.8<br>3.5 | 3.0<br>2.7 | 2.6<br>2.2 |

### Notes

- 1. Lead shoulder designs may vary.
- 2. Dimension includes excess dambar.

|  | OUTLINE |     | REFER           | EUROPEAN | ISSUE DATE |            |                                 |
|--|---------|-----|-----------------|----------|------------|------------|---------------------------------|
|  | VERSION | IEC | JEDEC           | JEITA    |            | PROJECTION | ISSUE DATE                      |
|  | SOT78   |     | 3-lead TO-220AB | SC-46    |            |            | <del>08-04-23</del><br>08-06-13 |

4Q Triad

# 12. Legal information

#### Data sheet status

| Document status [1][2]                | Product status [3] | Definition  |  |  |
|---------------------------------------|--------------------|---|--|--|
| Objective<br>[short] data<br>sheet    | Development        | This document contains data from the objective specification for product development. |  |  |
| Preliminary<br>[short] data<br>sheet  | Qualification      | This document contains data from the preliminary specification.                       |  |  |
| Product Production [short] data sheet |                    | This document contains the product specification.                                     |  |  |

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